
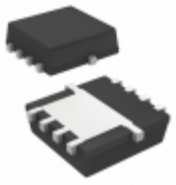
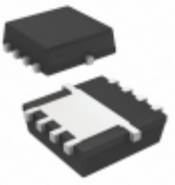
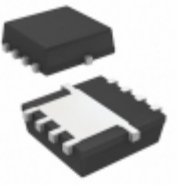

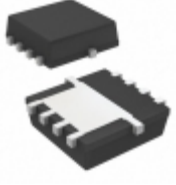



	<h2>SI7613DN-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7613DN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 35A 1212-8 PPAK</p> <p>Datenblätter:  SI7613DN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 43626 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7613DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 35A 1212-8 PPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	43626 pcs Stock
Hersteller Standard Vorlaufzeit	32 Weeks
detaillierte Beschreibung	P-Channel 20V 35A (Tc) 3.8W (Ta), 52.1W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-50°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.8W (Ta), 52.1W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	8.7 mOhm @ 17A, 10V
VGS (th) (Max) @ Id	2.2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	87nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2620pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±16V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7613DN-T1-GE3TR

SI7613DN-T1-GE3 ist neu im Original, Suche SI7613DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7613DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7613DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7611DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 40V 18A 1212-8</p>	 <p>SI7613DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8 PPAK</p>	 <p>SI7615ADN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8S</p>	 <p>SI7615ADN VISHAY VISHAY DFN33</p>
 <p>SI7615ADN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 35A 1212-8S</p>	 <p>SI7611DN-T1-E3 VISHAY SI7611DN-T1-E3 VISHAY</p>	 <p>SI7611DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 40V 18A 1212-8</p>	 <p>SI7615CDN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8</p>

heiße Teile

Mehr

SI7483DP-T1	SI7483DP-T1-E3	SI7483DP-T1-GE3	SI7485DP-T1-E3	SI7485DP-T1-E3
SI7485DP-T1-GE3	SI7485DP-T1-GE3	SI7489DP	SI7489DP-T1-GE3	SI7489DP-T1-GE3
SI7491DP	SI7491DP-T1-GE3	SI7491DP-T1-GE3	SI7501DN-T1-E3	SI7501DN-T1-E3
SI7540ADP-T1-GE3	SI7540ADP-T1-GE3	SI7540DP-T1-E3	SI7540DP-T1-E3	SI7540DP-T1-GE3
SI7540DP-T1-GE3	SI7606DN-T1-E3	SI7606DN-T1-GE3	SI7611DN-T1-GE3	SI7611DN-T1-GE3
SI7613DN-T1-GE3	SI7615ADN-T1-GE3	SI7615ADN-T1-GE3	SI7615DN	SI7615DN-T1-E3
SI7615DN-T1-GE3	SI7615DN-T1-GE3	SI7617DN-T1-GE3	SI7617DN-T1-GE3	SI7619DN-T1-GE3
SI7619DN-T1-GE3	SI7621DN-T1-GE3	SI7621DN-T1-GE3	SI7625DN-T1-GE3	SI7625DN-T1-GE3
SI7629DN-T1	SI7629DN-T1-GE3	SI7629DN-T1-GE3	SI7633DP-T1-GE3	SI7633DP-T1-GE3
SI7634BDP	SI7634BDP-T1-E3	SI7634BDP-T1-E3	SI7634BDP-T1-GE3	SI7634BDP-T1-GE3

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